

Spec. No.: C302S Issued Date: 2004.11.26 Revised Date:

Page No. : 1/4

Small Signal Schottky diode

BAT54S2

Description

Planar silicon Schottky barrier diode encapsulated in a SOD-323 very small plastic SMD package.

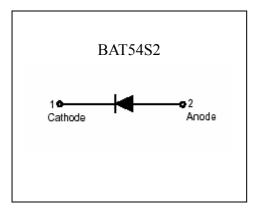
Features

- •Guard ring protected
- •Low forward voltage drop
- •Very small plastic SMD package

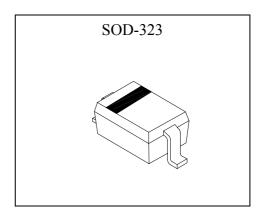
Applications

- •Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes

Symbol



Outline





Spec. No. : C302S Issued Date : 2004.11.26 Revised Date :

Page No. : 2/4

Absolute Maximum Ratings

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	continuous reverse voltage		-	30	V
IF	continuous forward current		-	200	mA
Ifrm	repetitive peak forward current	tp≤1s, δ≤0.5	-	300	mA
Ifsm	non-repetitive peak forward current	tp<10ms	-	600	mA
Ptot	total power dissipation	Tamb≤25°C	-	200	mW
Tstg	storage temperature		-65	+150	$^{\circ}\!\mathbb{C}$
Tj	junction temperature		-	125	$^{\circ}\!\mathbb{C}$
Tamb	operating ambient temperature		-65	+125	$^{\circ}\!\mathbb{C}$

Characteristics (Ta=25°C, unless otherwise specified)

Parameter	meter Symbol Condition		Min.	Max.	Unit
Reverse Breakdown Voltage	VBR	I _R =100μA	30	-	V
	Vr(1)	I _F =0.1mA	-	240	mV
	V _F (2)	I _F =1mA	-	320	mV
Forward Voltage (Note 1)	V _F (3)	I _F =10mA	-	400	mV
	V _F (4)	I _F =30mA	-	500	mV
	V _F (5)	I _F =100mA	-	800	mV
Reverse Leakage Current (Note 2)	everse Leakage Current (Note 2) IR VR=25V		-	2	μΑ
Diode Capacitance	CD	V _R =1V, f=1MHz	-	10	pF
Reverse Recovery Time	trr	when switched from I _F = 10mA to I _R =10mA; R _L =100Ω; measured at I _R =1mA	-	5	ns

Notes: 1.pulse test, tp=380µs, duty cycle<2%. 2.pulse test, tp=300µs, duty cycle<2%.

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
Rth j-a	thermal resistance from junction to ambient	note 1	635	K/W

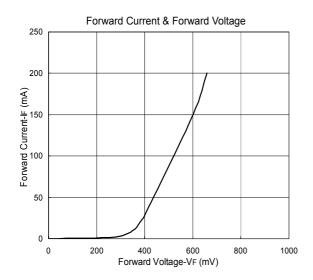
Note 1: Device mounted on a FR-4 PCB

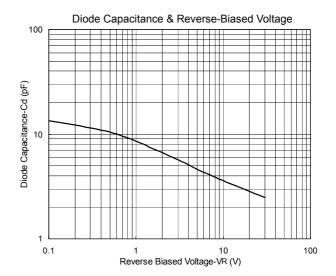


Spec. No. : C302S Issued Date : 2004.11.26

Revised Date : Page No. : 3/4

Characteristic Curves



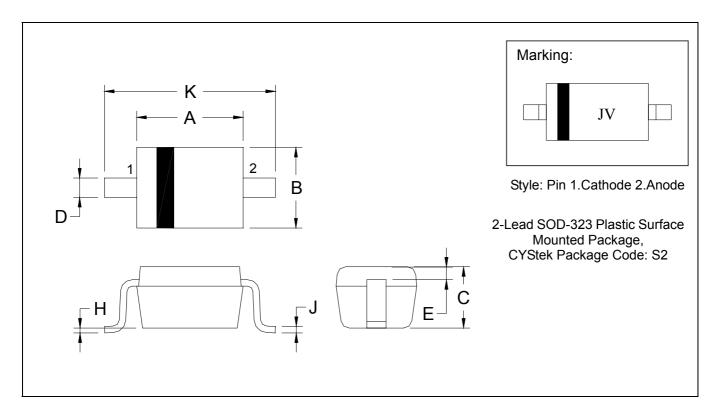




Spec. No.: C302S Issued Date: 2004.11.26 Revised Date:

Page No.: 4/4

SOD-323 Dimension



*: Typical

DIM	Inches		Millim	Millimeters		Inches		Millimeters	
	Min.	Max.	Min.	Max.	DIM	Min.	Max.	Min.	Max.
Α	0.0630	0.0709	1.60	1.80	Е	0.0060 REF		0.15 REF	
В	0.0453	0.0531	1.15	1.35	Н	0.0000	0.0040	0.00	0.10
С	0.0315	0.0394	0.80	1.00	J	0.0035	0.0070	0.089	0.177
D	0.0098	0.0157	0.25	0.40	K	0.0906	0.1063	2.30	2.70

Notes: 1.Controlling dimension: millimeters.

- 2.Lead thickness specified per L/F drawing with solder plating.
- 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.